1992 GaAs REL WORKSHOP PROGRAM
OCTOBER 4, 1992 FONTAINEBLEAU HOTEL, MIAMI BEACH, FLORIDA

SESSION I LIFE TESTING W.J. Roesch, Chair

METHOD FOR RAPID DETERMINATION OF ACTIVATION ENERGY AND LIFETIME FROM ACCELERATED STRESSING OF A SINGLE DEVICE: THEORY AND EXPERIMENT; B. Yeats, Hewlett Packard.

ROLE OF SUBSTRATE CURRENTS IN MMIC HIGH TEMPERATURE LIFE TESTING;
K.A. Christianson and W.T. Anderson, Naval Research Laboratory.

STUDY OF DRIFT IN A MESFET-BASED VARIABLE VOLTAGE ATTENUATOR MMIC;
P.L. Dreike, D.L. Barton, and C.E. Sandoval, Sandia National Laboratories.

HIGHLY RELIABLE GaAs MMICS; K. Decker, M. Loy, and D. Ragle, Texas Instruments.

SESSION II QUALITY ASSURANCE/BURN-IN W.T. Anderson, Chair

GaAs IC RELIABILITY RETURNS, A STORY OF ABUSE;
W.J. Roesch, A.L. Rublacava, and R.A. Winters, TriQuint Semiconductor.

ESD TESTING OF GaAs MMIC DEVICES; D.S. Lehr, P.N. Ersland, WA-COM, and A.K. Kreider, AT&T Bell Labs.

DIE SHEAR TESTING OF GALLIUM ARSENIDE;
M. Longwell, Texas Instruments, Incorporated, J. L. Cheever, ITT.

DC BIASED BURN-IN OF GaAs MMIC POWER AMPLIFIER ASSEMBLIES;
P. Ersland, D. Lahr, R. Higgins, D. Wells, V. Pelliccia, J-P. Lantari, M/A-COM, and K. Kreider, AT&T Bell Labs.

BURN-IN OF GaAs lCs; W. J. Roesch, TriQuint Semiconductor.

SESSION III OPEN DISCUSSIONS IS BURN NECESSARY? W.J. Roesch, Moderator

SESSION IV THERMAL EFFECTS W.J. Koziarz, Chair

DETERMINATION OF FET THERMAL RESISTANCE FROM DC IDMAX DATA; B. Yeats, Hewlett Packard

A RELIABILITY STUDY ON A BURIED PLATED HEAT SINK STRUCTURE FOR HIGH POWER GaAs MMICS;
K. Hosogi, T. lshkawa, M. Katsumata, K. Nishkani, M. Otsubo, and S. Mitsui, Mitsubishi Electric Corporation.

SOURCE-DRAIN BURN-OUT OF POWER GaAs FET;
T. Fujioka, M. Kohno, M. Yamanouchi, T. Sorioda, S. Takamiya, and Y. Kashimoto, Mitsubishi Electric Corporation.

RELIABILITY COMPARISON OF BERYLLIUM VERSUS CARBON FOR GaAs

PLANAR DOPED BARRIER DIODES, Y. Anand, M/A-COM, and R.J. Makik, AT&T Bell Laboratories.

SESSION V SPACE QUALIFICATION K.J. Russell, Chair

SPACE QUALIFICATION OF GaAs MMICS; P.H. Bolbot, C.E. Lindsay, C.M. Buckle, E.I. Drummond, R.F.B. Conlon, GEC-Marconi Materials Technology Limited.

QUALIFICATION OF GaAs POWER MESFETs FOR SPACE APPLICATIONS; E.
Nhan, K. Chao, R.H. Maurer, AND C.B. Bargeron, The Johns Hopkins University, Applied Physics Laboratory.

SINGLE EVENT UPSET CONCERNS IN GaAs DIGITAL CIRCUITS; T.R. Weatherford, SFA, D. McMorrow, Naval Research Laboratory, W.R. Curtice, Curtis Consulting, A.B. Campbell, A.R. Knudson, Naval Research Laboratory.